



JST16Q

TRITC

JST16F-1200BW

Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	4	kV

($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value	-	-Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	50	mA

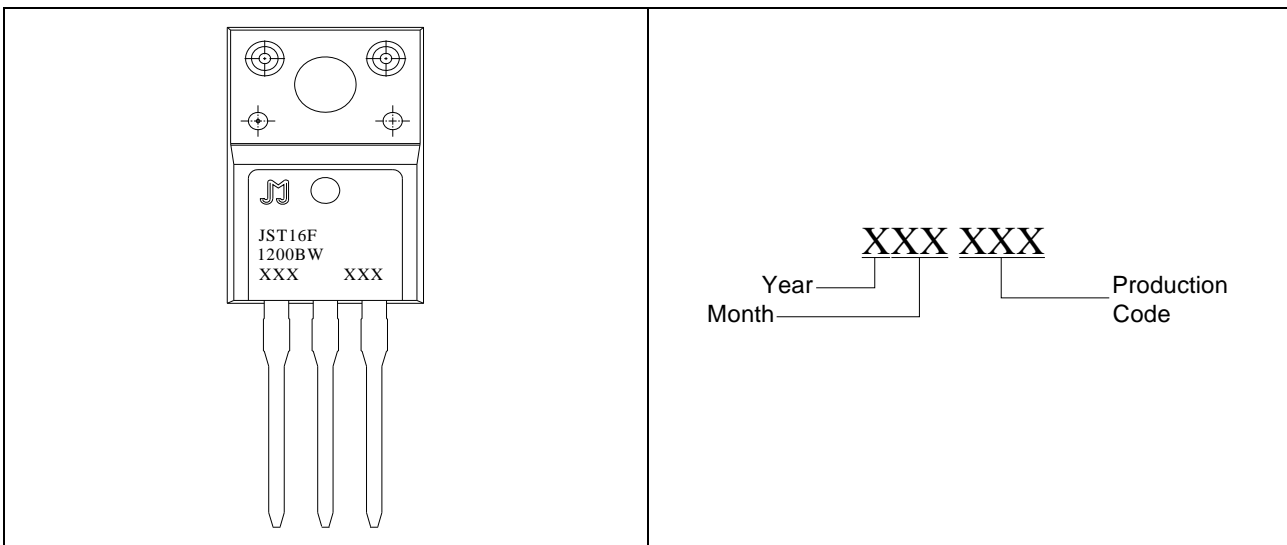
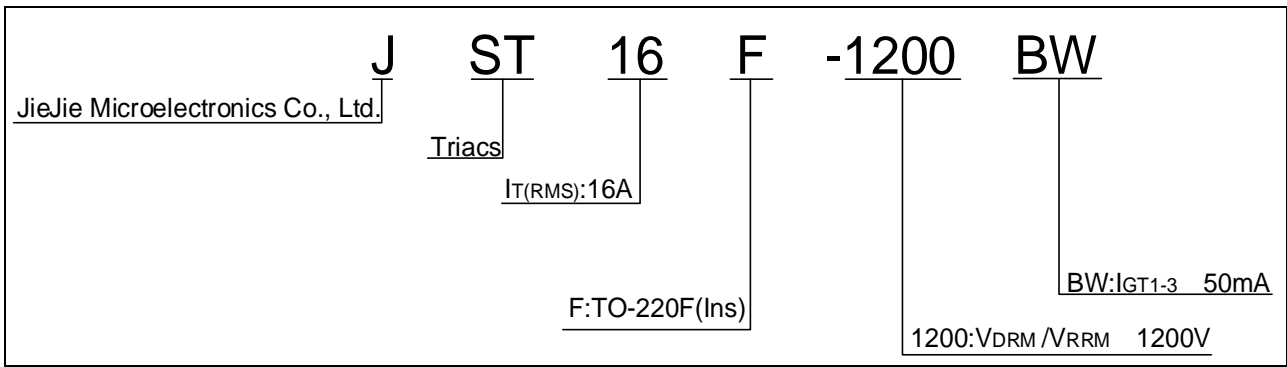


FIG.1: Maximum power dissipation versus RMS on-state current

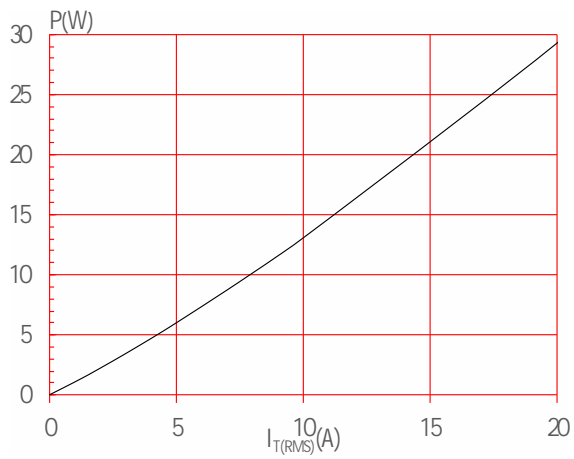


FIG.2: RMS on-state current versus case temperature

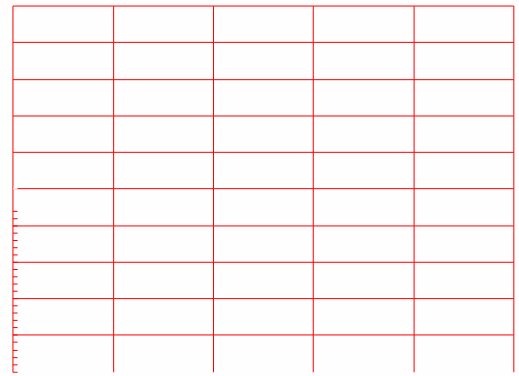


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA) -	Package	Base qty. (pcs)	Delivery mode
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